

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	206	(applied materials).as. and (((lookup or (look adj up)) adj table) or (bin with table) or (bin with algorithm))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/30 08:10
L4	98	(applied materials).as. and ((bin\$4 with table) or (bin\$4 with algorithm) or (bin\$4 with method))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/30 08:28
L5	2	"4345312".pn.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/30 08:43
L6	208	(applied materials).as. and (((lookup or (look adj up)) adj table) or (bin with table) or (bin\$4 with algorithm))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/30 08:47
L7	30744	(wafer or semiconductor) and ((bin\$4 with table) or (bin\$4 with algorithm) or (bin\$4 with method))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/30 08:56
L8	2493	(wafer or semiconductor) and ((bin\$4 with table) or (bin\$4 with algorithm) or (bin\$4 with method)) and (trim\$4)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/30 08:56
L9	191	(wafer or semiconductor) and ((bin\$4 with table) or (bin\$4 with algorithm) or (bin\$4 with method)) and (trim\$4 with value)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/30 09:08
L27	2408	(700/121).ccls.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/30 10:38
L28	1	"20020175384"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/30 10:52
S1	17685	(TOKYO same ELECTRON).as.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2009/09/24 09:19

S2	3449	((TOMOYASU same MASAYUKI) or (FUNK MERRITT LANE) or (PINTO KEVIN AUGUSTINE) or (ODAGIRI MASAYA) or (CHEN LEMUEL) or (YAMASHITA ASAO) or (IWAMI AKIRA) or (TAKAHASHI HIROYUKI)).in.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/24 09:22
S4	1	"20040185583"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/24 11:53
S5	8	10/229,446	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/24 14:08
S6	2	"20030045131"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/24 14:10
S7	0	METHODS AND APPARATUS FOR PROCESSING MICROELECTRONIC WORKPIECES USING METROLOGY	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/24 14:12
S8	2	(METHODS APPARATUS PROCESSING MICROELECTRONIC WORKPIECES USING METROLOGY).ti.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/24 14:12
S9	7	60/454,597	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/24 14:14
S10	6	("10705201" or "10705200" or "10704969" or "10705397")	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/24 15:38
S11	161	(TOKYO same ELECTRON).as. and metrology.dlm.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2009/09/24 16:22

S12	30	("4659220" "4869593" "4899055" "5042949" "5191393" "5258823" "5291269" "5486701" "5517032" "5604344" "5616063" "5695601" "5747813" "5757502" "5825498" "5835225" "5872633" "5943122" "5948203" "5957749" "6052188" "6108091" "6108092" "6111634" "6120348" "6142855" "6157450" "6184984" "6406641" "6413867").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/09/24 16:29
S13	1132033	WO "03021642"	US-PGPUB; USPAT; USOCR	OR	OFF	2009/09/24 16:32
S17	74	verbeke.in.	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/09/24 16:32
S18	16	verbeke.in. and WO	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/09/24 16:32
S19	113	verbeke.in.	US-PGPUB; USPAT; USOCR; EPO	ADJ	OFF	2009/09/24 16:34
S21	2	(WO "3021642") or (WO "204887") or (WO "2004084280")	US-PGPUB; USPAT; USOCR; EPO	ADJ	OFF	2009/09/24 16:36
S22	1	(WO "3021642") or (WO "204887") or (WO "4084280")	US-PGPUB; USPAT; USOCR; EPO	ADJ	OFF	2009/09/24 16:36
S23	2	(WO "3021642") or (WO "0204887") or (WO "2004084280")	US-PGPUB; USPAT; USOCR; EPO	ADJ	OFF	2009/09/24 16:36
S24	2	(WO "3021642") or (WO "204887") or (WO "2004084280")	US-PGPUB; USPAT; USOCR; EPO	ADJ	OFF	2009/09/24 16:38
S25	3	("6165805" "6438441" "5240556").pn.	US-PGPUB; USPAT; USOCR; EPO	ADJ	OFF	2009/09/24 16:48
S26	949	(TOKYO same ELECTRON). as. and (metrology or measur\$3).clm.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2009/09/24 17:23
S27	7	"6960416"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2009/09/24 18:22

S28	245	(control and (strategy and plan) and recipe) and semiconductor	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2009/09/25 16:53
S29	1	oxidized Tunable Etch Resistant ARC (TERA)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/25 17:09
S30	2543	oxidized Tunable Etch Resistant ARC or (TERA)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/25 17:09
S31	2543	(oxidized Tunable Etch Resistant ARC) or (TERA)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/25 17:09
S32	1	(oxidized Tunable Etch Resistant ARC)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/25 17:09
S34	59	(Tunable Etch Resistant ARC) or (tera material)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/25 17:11
S35	315	wall heating (element or lamp or apparatus)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/28 16:44
S36	12	wall heating (element or lamp or apparatus) and wafer	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/28 16:51
S37	5506	(TOKYO same ELECTRON). as. and pressure	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2009/09/29 07:53
S38	876	(TOKYO same ELECTRON). as. and (low adj pressure)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2009/09/29 07:53
S39	112	(TOKYO same ELECTRON). as. and (low adj pressure with ("10" or "100" or "75"))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2009/09/29 07:54
S40	49	(TOKYO same ELECTRON). as. and (low adj pressure with ("10" or "100" or "75")) and mtorr	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2009/09/29 07:55
S42	32365	(low adj pressure) with process\$3	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2009/09/29 08:00

S43	42	(TOKYO same ELECTRON). as. and (low adj pressure with ("10" or "100" or "75")) and mtorr and temperature	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2009/09/29 08:01
S44	23	(TOKYO same ELECTRON). as. and (low adj pressure with ("10" or "100" or "75")) and mtorr and (temperature with gas)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2009/09/29 09:37
S45	53295	temperature process gas	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	WITH	OFF	2009/09/29 09:44
S46	1213	(TOKYO same ELECTRON). as. and S45	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2009/09/29 09:44
S50	231	(TOKYO same ELECTRON). as. and S45 and (distribution system)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	WITH	OFF	2009/09/29 09:45
S51	75	(thermal treatment chamber) and (temperature with ("10" or "50"))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 09:58
S52	4	US-6284086-\$.DID. OR US- 4838978-\$.DID. OR WO- 0178517-\$.DID. OR US- 4492618-\$.DID. OR US- 5273588-\$.DID.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 10:40
S53	3	US-6284006 -\$.DID. OR US- 4838978-\$.DID. OR WO- 0178517-\$.DID. OR US- 4492610-\$.DID. OR US- 5273588-\$.DID. OR 2002/195201 OR 2002/802947 OR US- 5273588-\$.DID. OR 2002/811216	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 10:47
S54	125	"6284006" OR "4838978" OR WO-0178517 OR "4492610" OR "5273588" OR 2002/195201 OR 2002/802947 OR "5273588" OR WO-2002/811216	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 10:49
S55	125	"6284006" OR "4838978" OR (WO-0178517) OR "4492610" OR "5273588" OR 2002/195201 OR 2002/802947 OR "5273588" OR (WO-2002/811216)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 10:49

S56	4	("6284006" OR "4838978" OR (WO-0178517) OR "4492610" OR "5273588" OR 2002/195201 OR 2002/802947 OR "5273588" OR (WO-2002/811216)).pn.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 10:50
S57	55	(thermal treatment chamber) and (low with temperature)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 10:55
S58	22	"5240556"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 11:02
S59	347	((Ishikawa Yoshio) or (arami Junichi) or (Ikeda Towl) or (Iwata Teruo)).in.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 11:06
S60	3038366	temperature	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 11:06
S61	95	S59 and S60	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 11:07
S62	1	"5484483" .pn.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 11:16
S63	53	"5221403"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 11:21
S64	53	"5,221,403"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 11:44
S65	0	eric strang	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 13:24
S66	120	(eric same strang).in.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 13:24
S67	2	"20030045131" and (temperature and gas)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 14:35

S68	1769	gas distribution system and temperature	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 14:46
S69	1481	gas distribution system and temperature and (wafer or chamber or semiconductor)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 14:50
S70	521	((gas distribution system) same temperature) and (wafer or chamber or semiconductor)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 14:58
S71	726	((thermal treatment chamber) or (process space same chamber) and (temperature)) and (wafer or substrate or workpiece or (work piece))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 16:03
S72	726	((thermal treatment chamber) or (process space same chamber) and (temperature)) and (wafer or substrate or workpiece or (work piece))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 16:03
S73	3	US-4898798-\$.DID. OR US-5303671-\$.DID. OR US-5254505-\$.DID. OR US-438785D-\$.DID.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 16:24
S74	5	US-6544380-\$.DID. OR US-5634551-\$.DID. OR US-6616767-\$.DID. OR US-1912152-\$.DID. OR US-6515261-\$.DID.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 16:29
S75	72	thermal treatment chamber with temperature	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 16:44
S76	1	"20040185583".pn.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 17:08
S77	10	US-6884734-\$.DID. OR US-6926843-\$.DID. OR US-20040191998-\$.DID. OR US-4381300-\$.DID. OR US-20050218113-\$.DID. OR US-20050227494-\$.DID. OR US-20040097047-\$.DID. OR US-20040185583-\$.DID. OR US-122004D-\$.DID. OR US-20040110354-\$.DID. OR US-5282925-\$.DID.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 17:11

S78	8021	trim\$4 with amount	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 17:18
S79	0	determin43 same trim\$4 with amount	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 17:18
S80	997	determin\$3 same trim\$4 with amount	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 17:19
S81	367	determin\$3 same trim\$4 with amount and (wafer or substrate or workpiece or (work piece) or semiconductor)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	OFF	2009/09/29 17:19
S82	2	"20030045131"	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2009/09/29 18:01
S83	5	US-5769952-\$.DID. OR US- 5368054-\$.DID. OR US- 6745637-\$.DID. OR US- 6267122-\$.DID. OR US- 20010024691-\$.DID.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/29 18:58
S84	3	US-5672239-\$.DID. OR US- 5776360-\$.DID. OR US- 6467491-\$.DID. OR EP- 0998170-\$.DID.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	SAME	OFF	2009/09/29 19:01

EAST Search History (Interference)

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